



FIG.3A

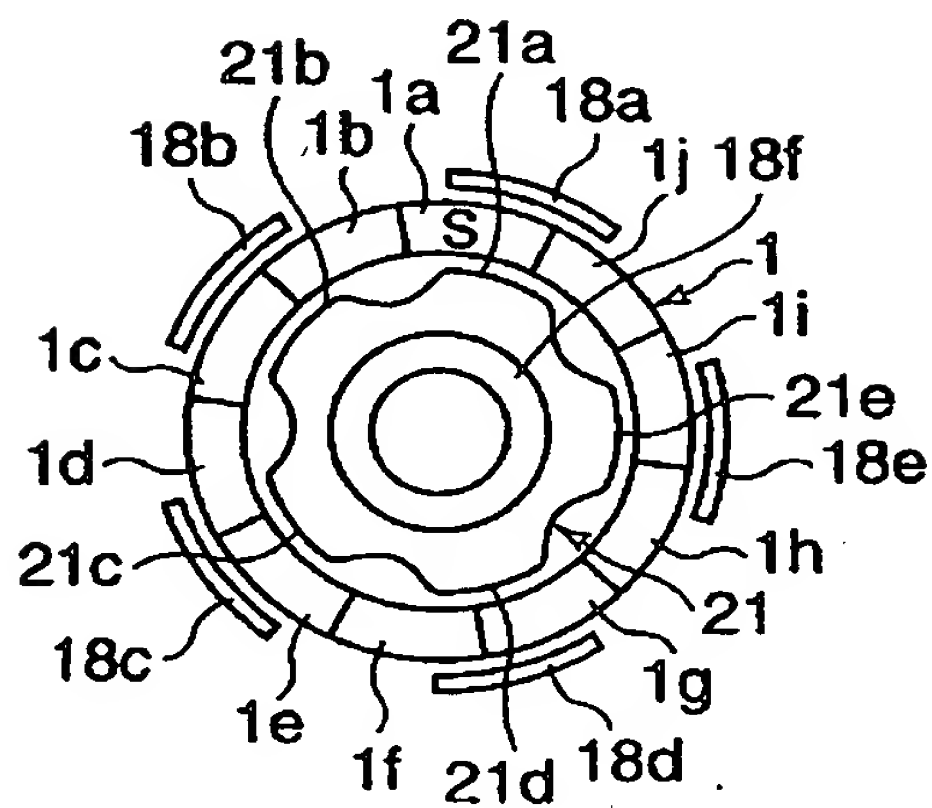


FIG.3B

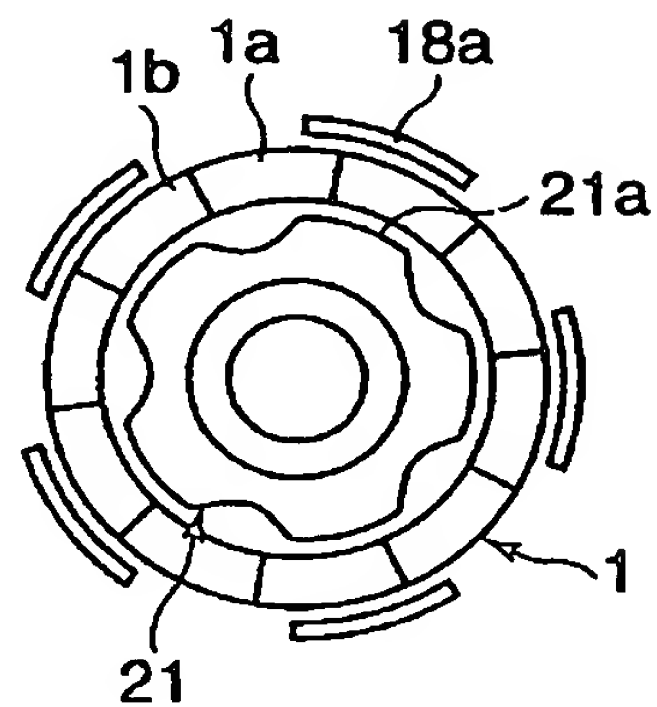


FIG.3C

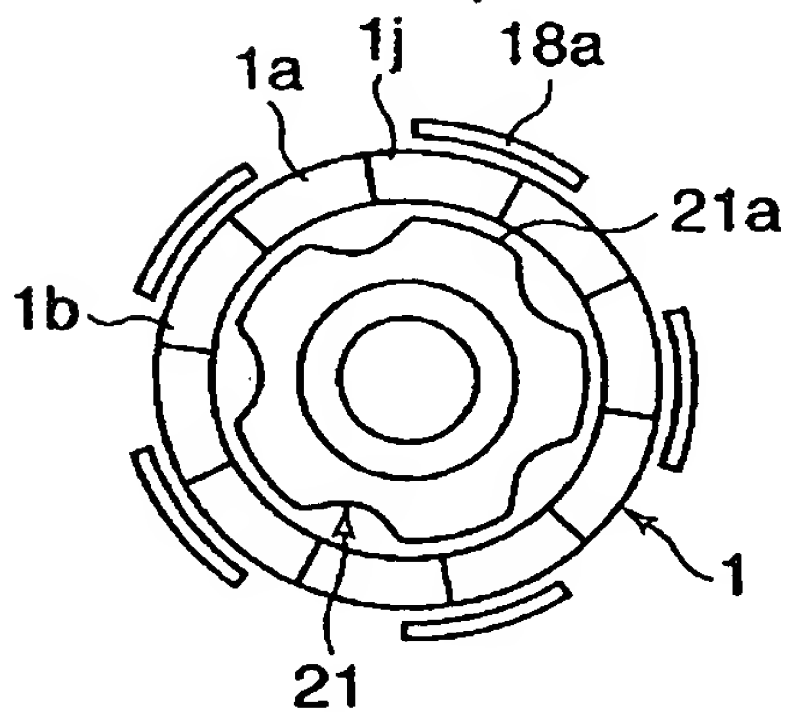


FIG.3D

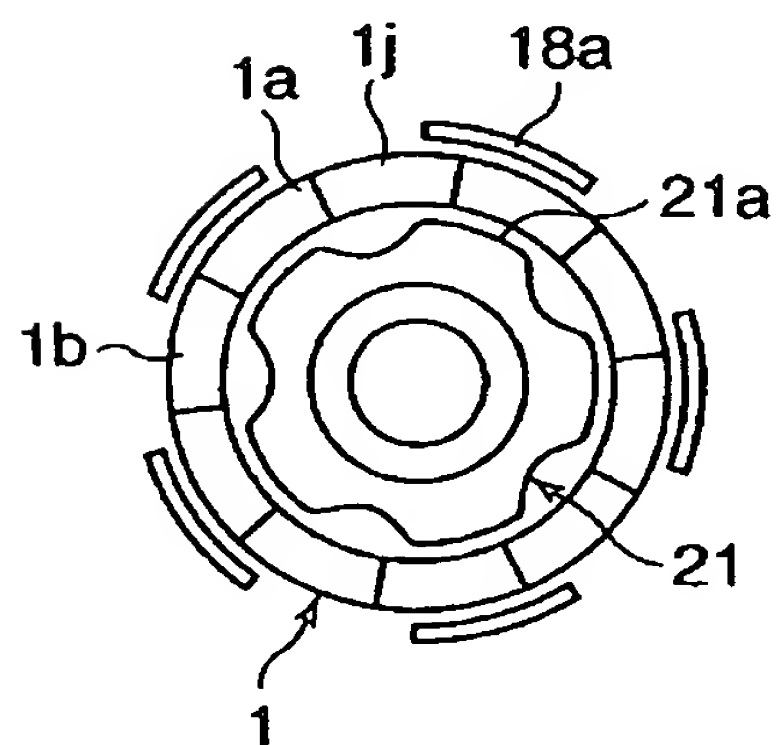
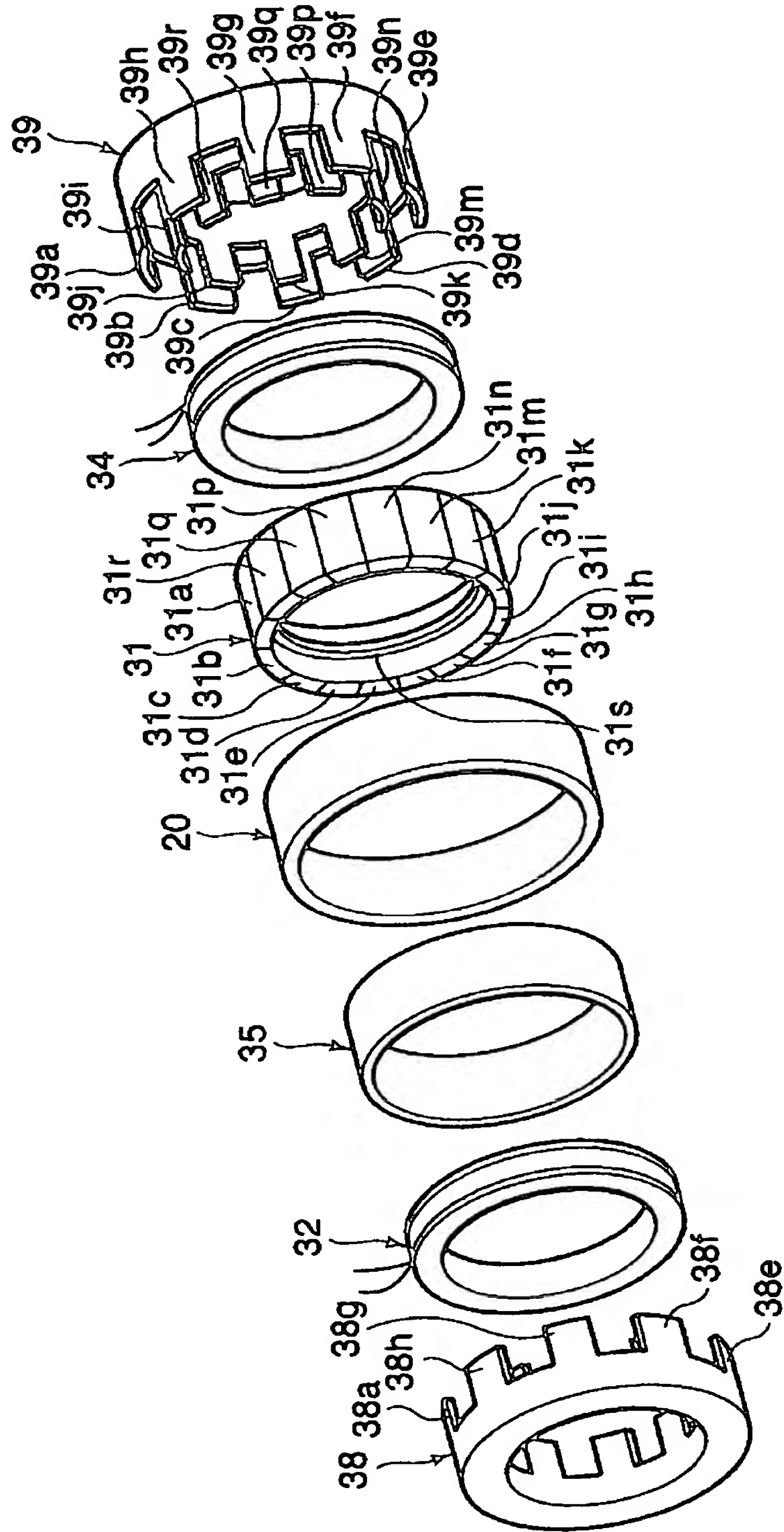




FIG. 8



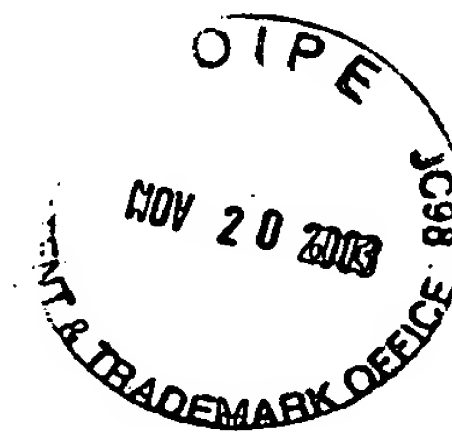


FIG. 14A

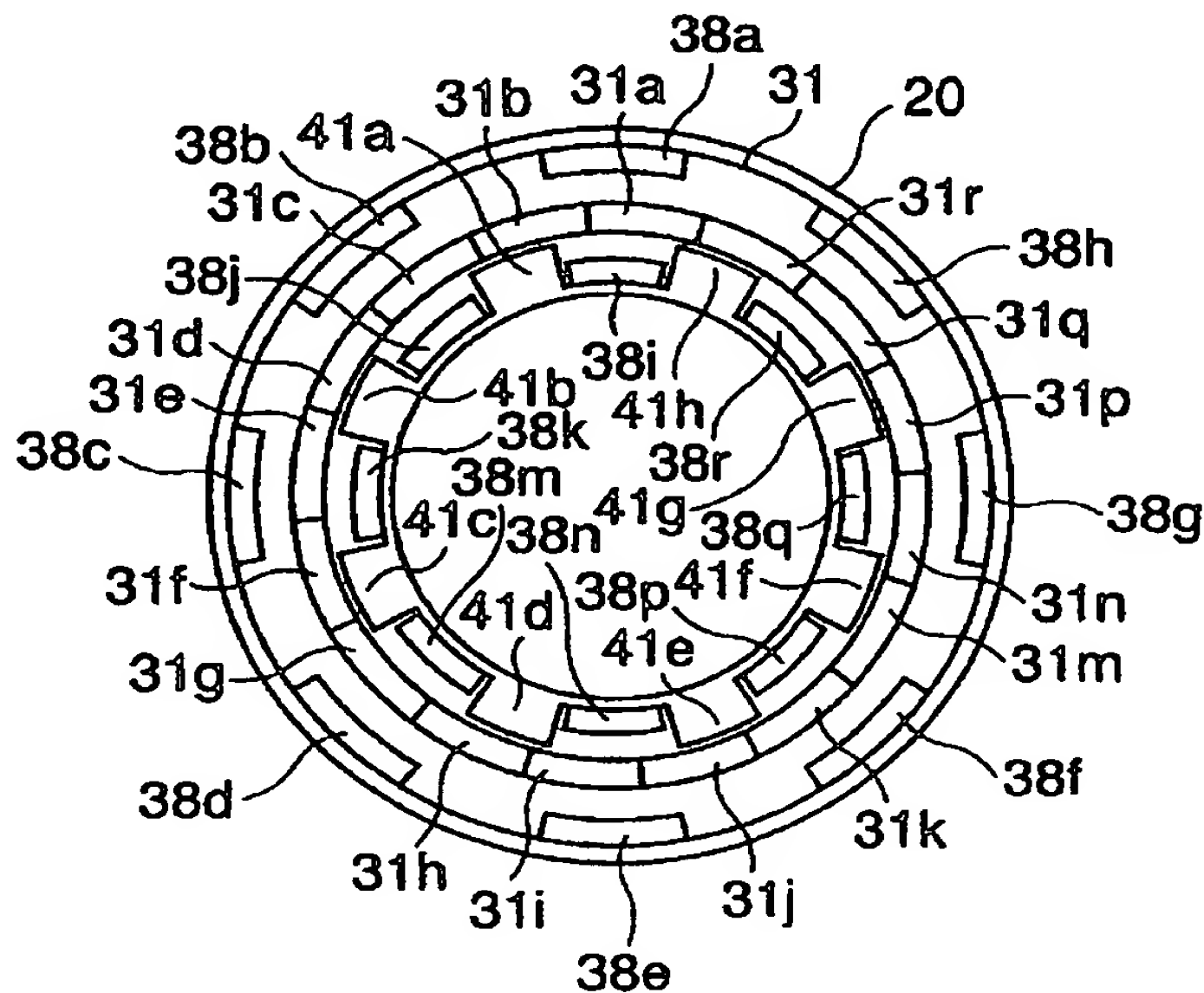


FIG. 14B

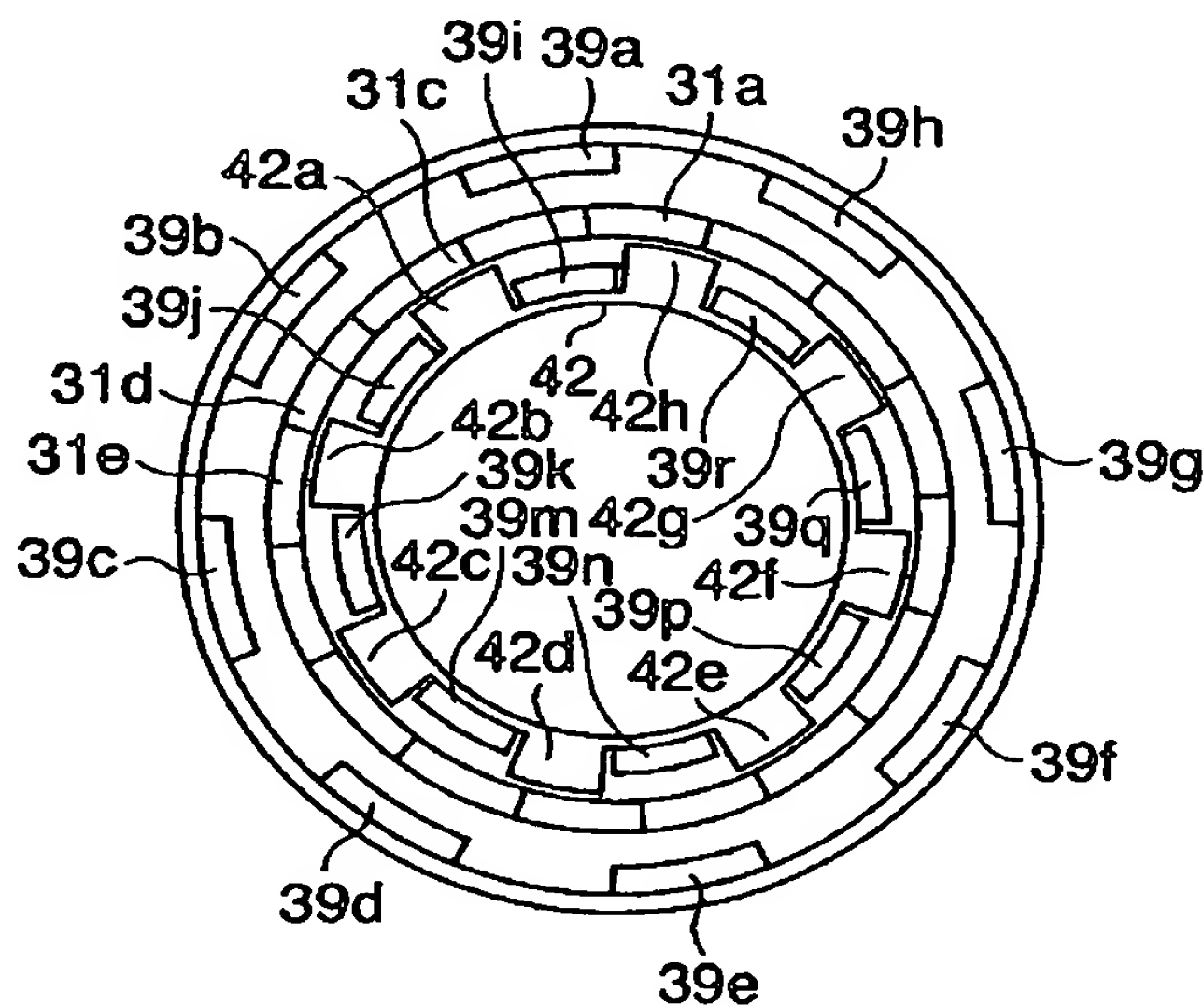


Fig. 3 is a cross-sectional view of the semiconductor device 100. The device includes a central channel 311. On either side of the channel are gate electrodes 312 and 313. The gate electrodes are covered by a gate insulating layer 314. The channel 311 is covered by a channel insulating layer 315. The device is further covered by a top insulating layer 317. Various other layers and structures are labeled, including 314a, 314b, 314c, 314d, 314e, 315a, 315b, 315c, 315d, and 315e.